



HUF76633P3_F085 Information

Part Number HUF76633P3_F085

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N CH 100V 39A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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HUF76633P3_F085 Specifications

Manufacturer Part NumberHUF76633P3_F085ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-220-3SeriesAutomotive, AEC-Q101, UltraFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C39A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs67nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1820pF @ 25VVgs (Max)±16VFET Feature-Proves Dissipation (Max)145W (Tr)
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series Automotive, AEC-Q101, UltraFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 39A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single To-220-3 Automotive, AEC-Q101, UltraFET? Automotive, AEC-Q1
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FET Feature -
D Diiti (M)
Power Dissipation (Max) 145W (Tc)
Rds On (Max) @ Id, Vgs 35 mOhm @ 39A, 10V
Operating Temperature $-55^{\circ}\text{C} \sim 175^{\circ}\text{C} \text{ (TJ)}$
Mounting Type Through Hole
Supplier Device Package TO-220AB
Package / Case TO-220-3
Report errors?

HUF76633P3_F085 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

HUF76633P3_F085 Payment Methods





















HUF76633P3_F085 Shipping Methods













If you have any question about HUF76633P3_F085, please do not hesitate to contact us!

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